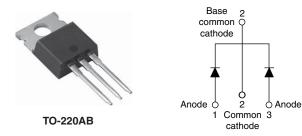


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PRODUCT SUMMARY					
Package	TO-220AB				
I _{F(AV)}	2 x 20 A				
V _R	150 V				
V_F at I_F	0.71 V				
I _{RM} max.	15 mA at 125 °C				
T _J max.	175 °C				
Diode variation	Common cathode				
E _{AS}	1.0 mJ				

FEATURES

- 175 °C T_J operation
- · Very low forward voltage drop
- · High frequency operation



• High purity, high temperature epoxy encapsulation for enhanced mechanical strength RoHS and moisture resistance



- Guard ring for enhanced ruggedness and long term reliability
- Compliant to RoHS Directive 2002/95/EC
- Designed and gualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)

DESCRIPTION

The VS-40CTQ... center tap Schottky rectifier has been optimized for very low forward voltage drop, with moderate leakage. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS			
I _{F(AV)}	Rectangular waveform	40	A			
V _{RRM}		150	V			
I _{FSM}	t _p = 5 μs sine	1500	A			
V _F	20 A_{pk} , T_J = 125 °C (per leg)	0.71	V			
TJ		- 55 to 175	°C			

VOLTAGE RATINGS				
PARAMETER	SYMBOL	VS-40CTQ150PbF	VS-40CTQ150-N3	UNITS
Maximum DC reverse voltage	V _R	150	150	V
Maximum working peak reverse voltage	V _{RWM}	150	150	v

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST COND	TEST CONDITIONS				
Maximum average per leg		50 % duty cyclo at $T_{-} = 140 ^{\circ}$ C	rootangular wavoform	20			
See fig. 5 per device	I _{F(AV)}	50 % duty cycle at T_C = 140 °C, rectangular waveform		40	А		
Maximum peak one cycle non-repetitive surge current per leg		5 μs sine or 3 μs rect. pulse	Following any rated load condition and with rated	1500	A		
See fig. 7	I _{FSM}	10 ms sine or 6 ms rect. pulse	V _{RRM} applied	250			
Non-repetitive avalanche energy per leg	E _{AS}	T _J = 25 °C, I _{AS} = 1.5 A, L = 0.9 mH		1.0	mJ		
Repetitive avalanche current per leg	I _{AR}	Current decaying linearly to zero in 1 μs Frequency limited by T_J maximum V_A = 1.5 x V_R typical		1.5	А		

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ELECTRICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS		
		20 A	T _{.1} = 25 °C	0.93	V		
Maximum forward voltage drop per leg See fig. 1	V _{FM} ⁽¹⁾	40 A	1j=25 0	1.16			
	VFM (1)	20 A	T _{.1} = 125 °C	0.71			
		40 A	1j = 125 C	0.85			
Maximum reverse leakage current per leg	I _{RM} ⁽¹⁾	T _J = 25 °C	$V_{\rm B}$ = Rated $V_{\rm B}$	50	μΑ		
See fig. 2	IRM W	T _J = 125 °C	VR - Haleu VR	15	mA		
Maximum junction capacitance per leg	CT	$V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHz) 25 °C		450	pF		
Typical series inductance per leg	L _S	Measured lead to lead 5 mm from package body		8.0	nH		
Maximum voltage rate of change	dV/dt	Rated V _R		10 000	V/µs		

Note

 $^{(1)}\,$ Pulse width < 300 $\mu s,\,duty\,cycle$ < 2 $\,\%$

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		- 55 to 175	°C
Maximum thermal resistance, junction to case per leg		P	DC operation See fig. 4	1.5	
Maximum thermal resistance, junction to case per package		R _{thJC}	DC operation	0.75	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5	
Annyovimoto weight				2	g
Approximate weight				0.07	oz.
Mounting torque	minimum		Non-lubricated threads	6 (5)	kgf · cm
Mounting torque —	maximum		Non-Iubricateu filleaus	12 (10)	(lbf · in)
Marking device			Case style TO-220AB	40CT	Q150



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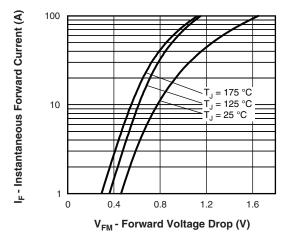
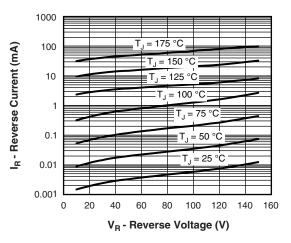
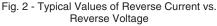


Fig. 1 - Maximum Forward Voltage Drop Characteristics





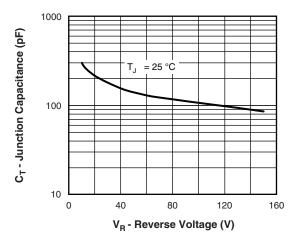
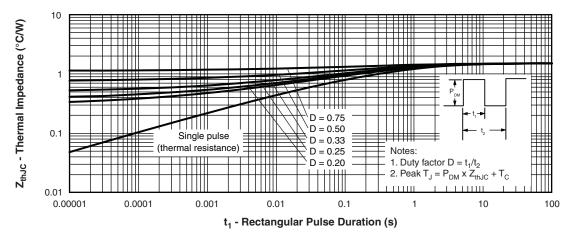


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

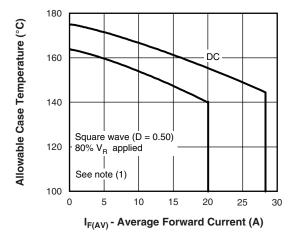


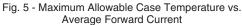


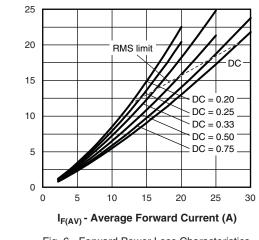
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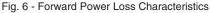


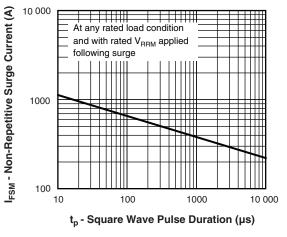
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Average Power Loss (W)

Fig. 7 - Maximum Non-Repetitive Surge Current

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $Pd = Forward power loss = I_{F(AV)} \times V_{FM} at (I_{F(AV)}/D)$ (see fig. 6); $Pd_{REV} = Inverse power loss = V_{R1} \times I_R (1 - D)$; $I_R at V_{R1} = 80 \% V_R$ applied



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ORDERING INFORMATION TABLE

Device code	VS-	40	С	т	Q	150	PbF	
		(2)	(3)	(4)	(5)	(6)	(7)	I
		Vial		oioonduu		duct	U	
	<u> </u>				ctors pro	auci		
	2 -	Cur	rent rati	ng (40 =	: 40 A)			
	3 -	Circ	uit conf	iguratior	ו:			
		C =	Commo	on catho	de			
	4 -	Pac	kage:					
		T =	TO-220)				
	5 -	Sch	ottky "C	" series				
	6 -	Volt	age rati	ngs (15	0 = 150	V)		
	7 -	Env	ironmer	ntal digit				
		• P	bF = Le	ad (Pb)	-free an	d RoHS	complia	ant
		i- •	√3 = Ha	logen-fr	ee, RoH	IS comp	oliant, ar	nd totally

-143 -	- nalogen-liee,	RUHS CUI	ipliant, and	totally lea	u (FD)-liee

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-40CTQ150PbF	50	1000	Antistatic plastic tube			
VS-40CTQ150-N3	50	1000	Antistatic plastic tube			

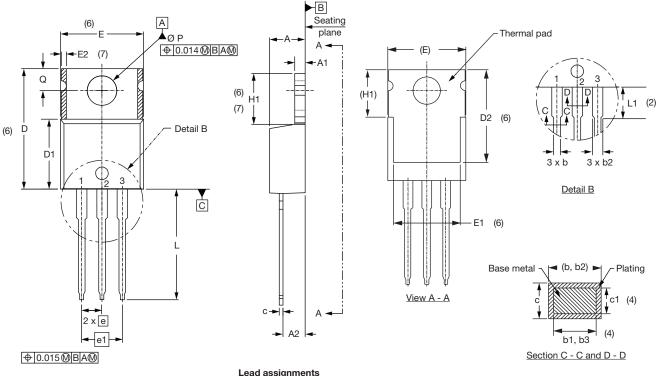
LINKS TO RELATED DOCUMENTS					
Dimensions		www.vishay.com/doc?95222			
Port marking information	TO-220AB PbF	www.vishay.com/doc?95225			
Part marking information	TO-220AB -N3	www.vishay.com/doc?95028			

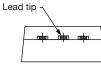


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TO-220AB

DIMENSIONS in millimeters and inches





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						-					
	_										

<u>Diodes</u> 1. - Anode/open 2. - Cathode

2.	-	Cathode
3.	-	Anode

SYMBOL	MILLIMETERS		INCHES		NOTES	Γ
	MIN.	MAX.	MIN.	MAX.	NOTES	
A	4.25	4.65	0.167	0.183		
A1	1.14	1.40	0.045	0.055		
A2	2.56	2.92	0.101	0.115]
b	0.69	1.01	0.027	0.040		1
b1	0.38	0.97	0.015	0.038	4	
b2	1.20	1.73	0.047	0.068		
b3	1.14	1.73	0.045	0.068	4]
С	0.36	0.61	0.014	0.024		
c1	0.36	0.56	0.014	0.022	4	
D	14.85	15.25	0.585	0.600	3	
D1	8.38	9.02	0.330	0.355		
D2	11.68	12.88	0.460	0.507	6	

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- ⁽³⁾ Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Dimension b1, b3 and c1 apply to base metal only
- ⁽⁵⁾ Controlling dimensions: inches
- $^{\rm (6)}$ Thermal pad contour optional within dimensions E, H1, D2 and E1

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. 0.414 10.11 10.51 0.398 Е 3,6 E1 6.86 8.89 0.270 0.350 6 E2 0.76 0.030 7 --2.41 2.67 0.095 0.105 е 0.208 e1 4.88 5.28 0.192 H1 6.09 6.48 0.240 0.255 6,7 13.52 14.02 0.532 0.552 Т 3.32 3.82 0.131 0.150 2 L1 ØΡ 3.54 3.73 0.139 0.147 0.102 Q 2.60 3.00 0.118 90° to 93° 90° to 93° θ

Conforms to JEDEC outline TO-220AB

- $^{(7)}$ Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- ⁽⁸⁾ Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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